



08NM65-FD

Power MOSFET

0.8A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

DESCRIPTION

The UTC **08NM65-FD** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics.

This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(on)} < 7.3\Omega @ V_{GS}=10V, I_D=0.4A$
- * High breakdown voltage

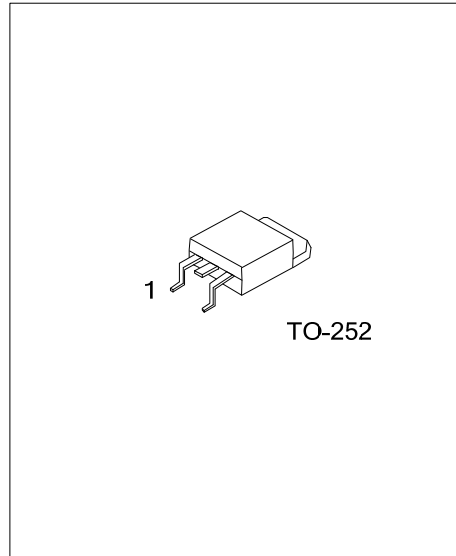
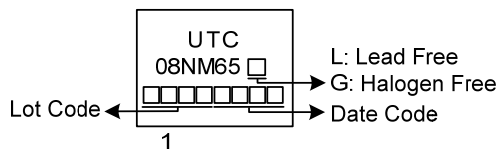
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
08NM65L-TN3-R	08NM65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>08NM65G-TN3-R</p> <p>(1) Packing Type (2) Package Type (3) Green Package</p>	<p>(1) R: Tape Reel (2) TN3: TO-252 (3) G: Halogen Free and Lead Free L: Lead Free</p>
---	--

MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A =25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V _{DSS}	650	V
Gate-Source Voltage	V _{GSS}	±30	V
Drain Current	Continuous	I _D	0.8
	Pulsed	I _{DM}	1.6
Peak Diode Recovery dv/dt (Note 3)	dv/dt	7.5	V/ns
Power Dissipation	P _D	28	W
Junction Temperature	T _J	+150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. I_{SD} ≤ 0.8A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	110	°C/W
Junction to Case	θ _{JC}	4.46	°C/W

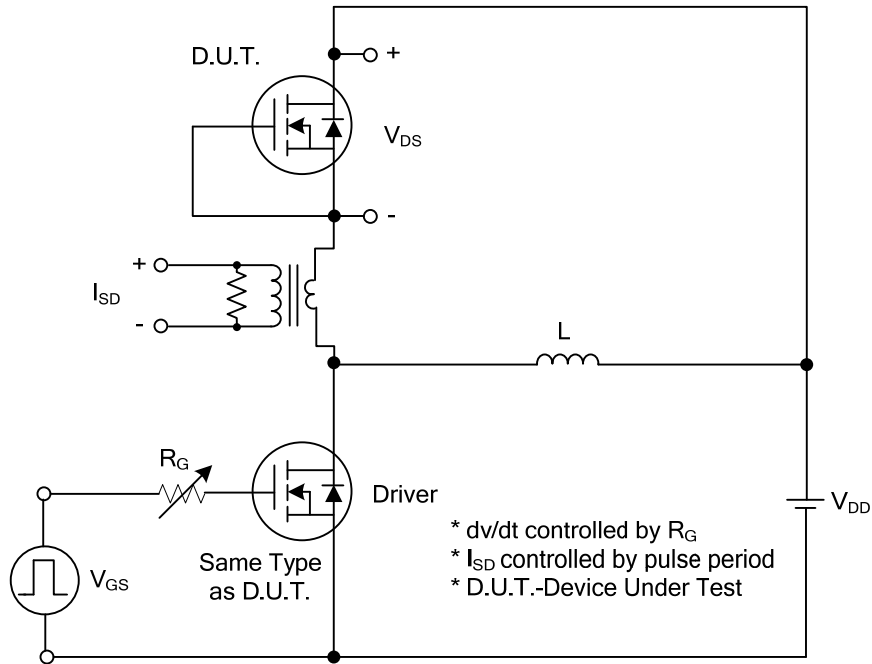
■ ELECTRICAL CHARACTERISTICS (T_C =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	1.0		3.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =0.4A			7.3	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		65		pF
Output Capacitance	C _{OSS}			47		pF
Reverse Transfer Capacitance	C _{RSS}			5		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q _G	V _{DS} =300V, V _{GS} =10V, I _D =0.8A, I _D =3mA (Note 1, 2)		8.5		nC
Gate to Source Charge	Q _{GS}			3		nC
Gate to Drain Charge	Q _{GD}			2.7		nC
Turn-ON Delay Time	t _{D(ON)}	V _{DS} =300V, V _{GS} =10V, I _D =0.8A, R _G =25Ω (Note 1, 2)		1.4		ns
Rise Time	t _R			9.2		ns
Turn-OFF Delay Time	t _{D(OFF)}			8.8		ns
Fall-Time	t _F			40		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I _S				0.8	A
Maximum Body-Diode Pulsed Current	I _{SM}				1.6	A
Drain-Source Diode Forward Voltage	V _{SD}	I _S =0.8A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time	t _{rr}	I _S =0.8A, V _{GS} =0V,		80		ns
Body Diode Reverse Recovery Charge	Q _{rr}	di _F /dt=100A/μs (Note 1)		0.18		μC

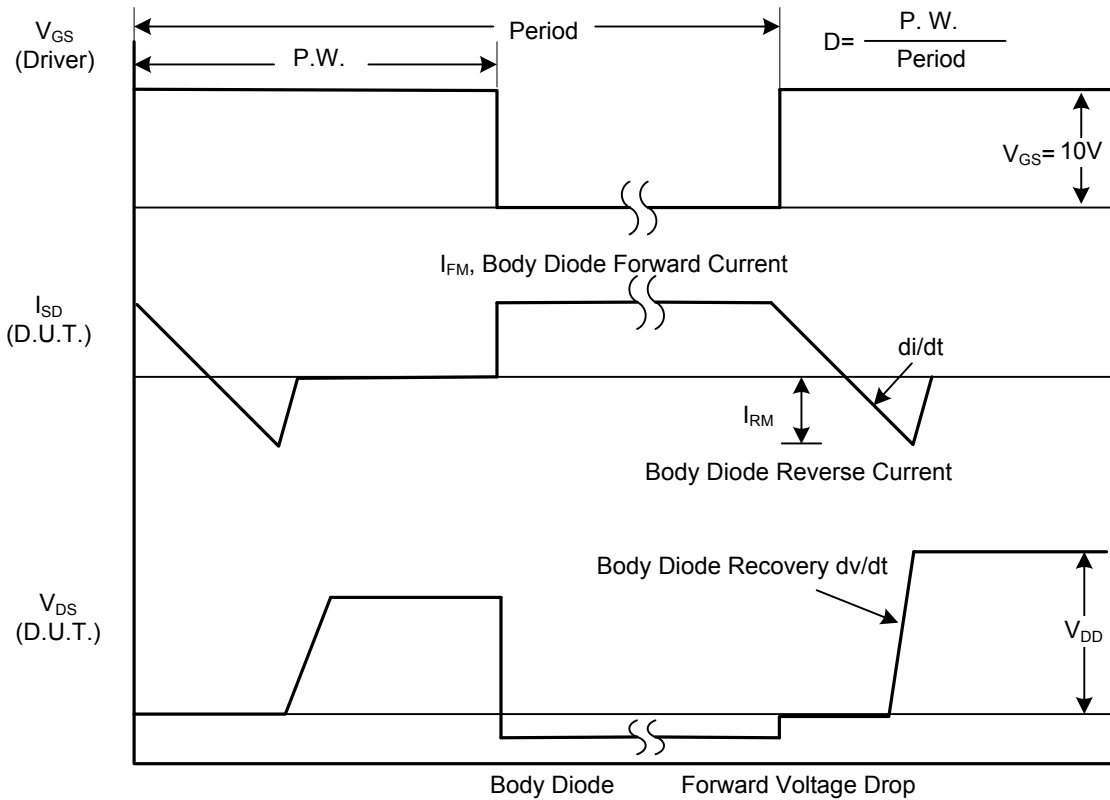
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

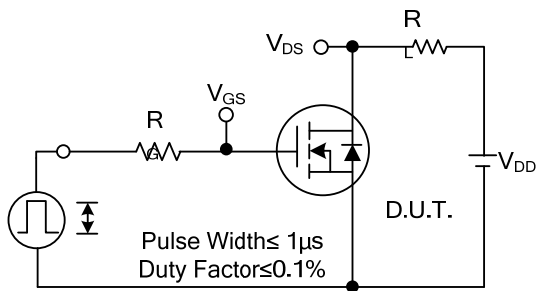


Peak Diode Recovery dv/dt Test Circuit

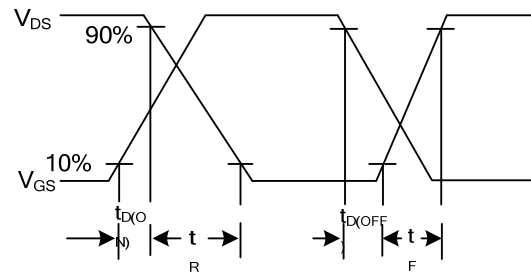


Peak Diode Recovery dv/dt Waveforms

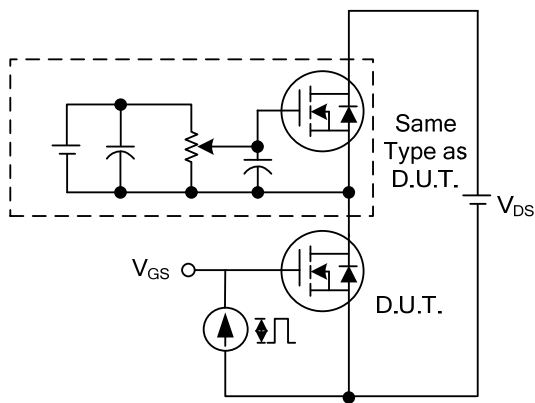
TEST CIRCUITS AND WAVEFORMS



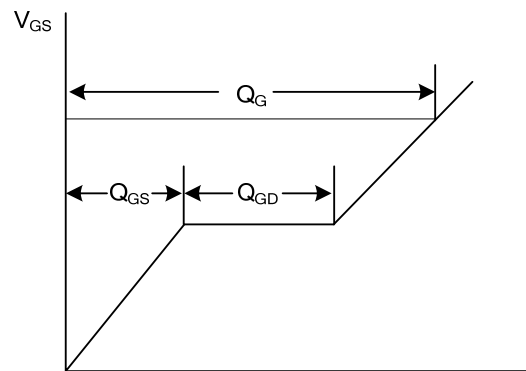
Switching Test Circuit



Switching Waveforms

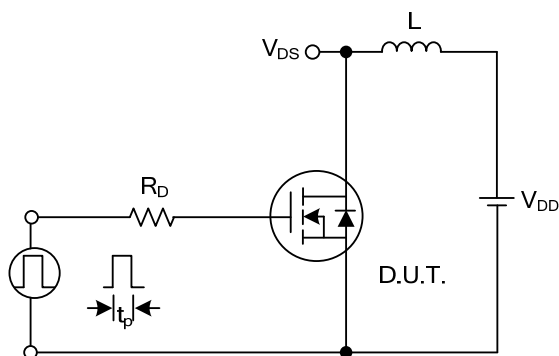


Gate Charge Test Circuit

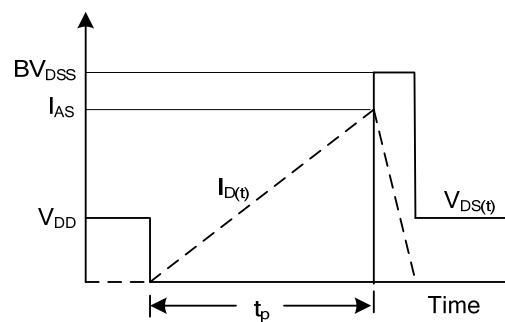


Charge

Gate Charge Waveform

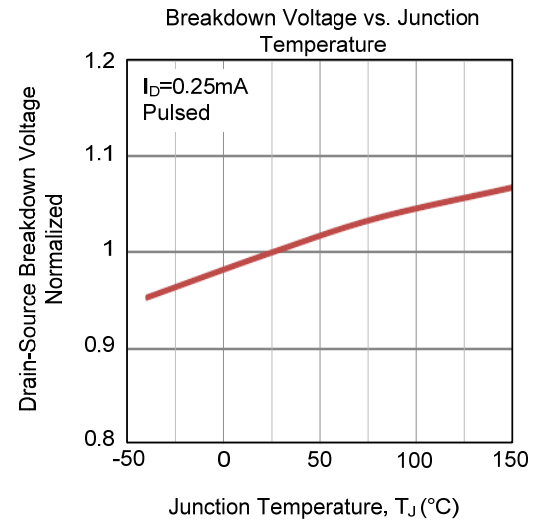
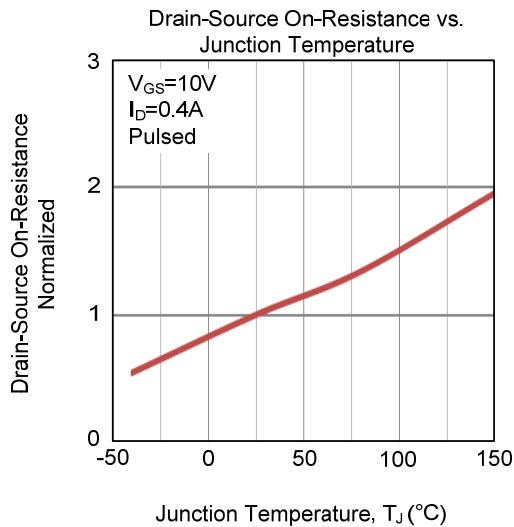
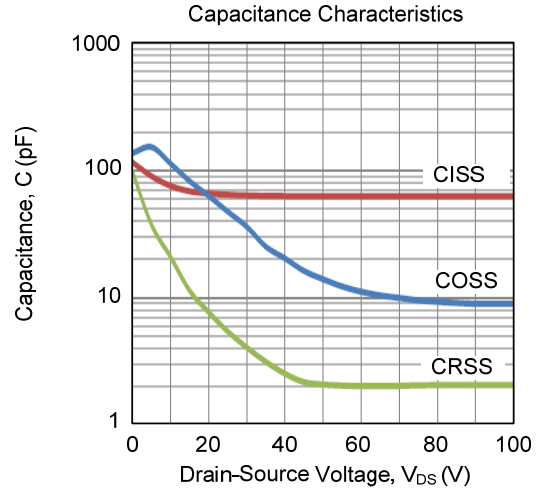
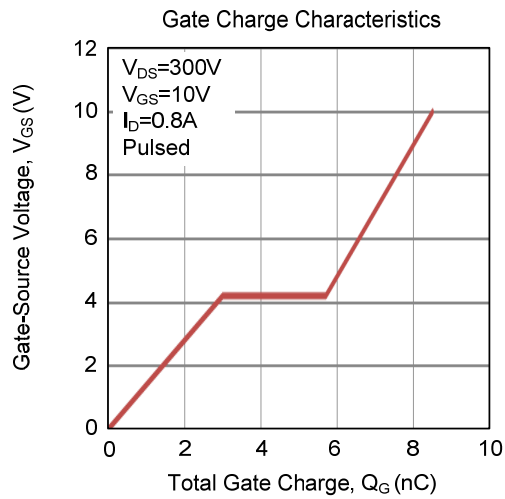
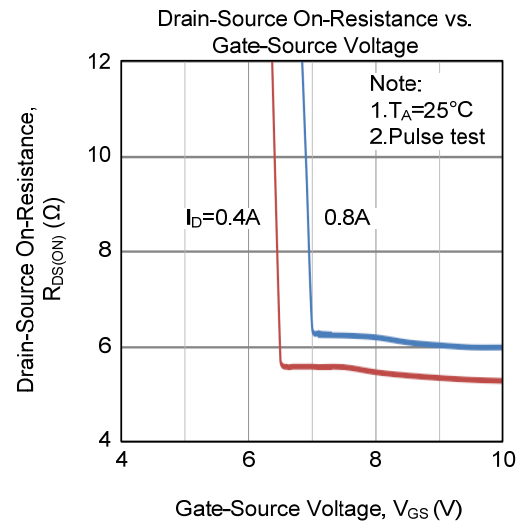
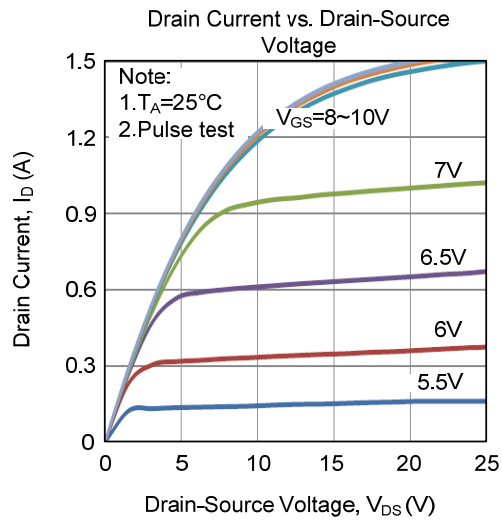


Unclamped Inductive Switching Test Circuit

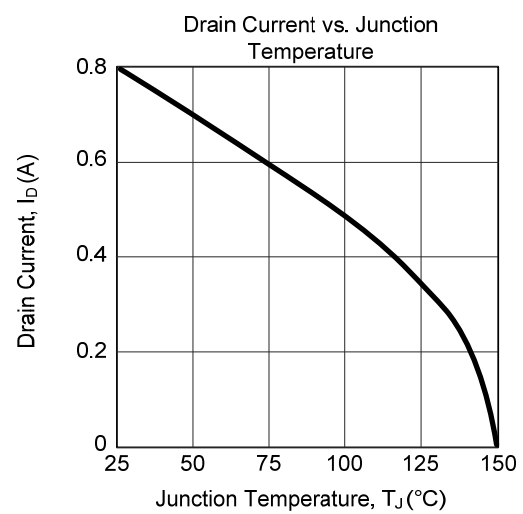
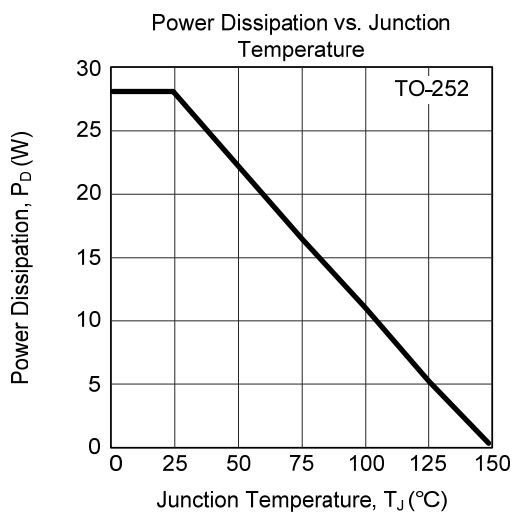
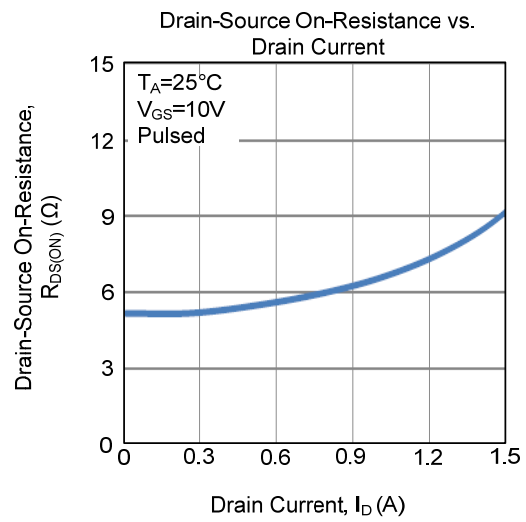
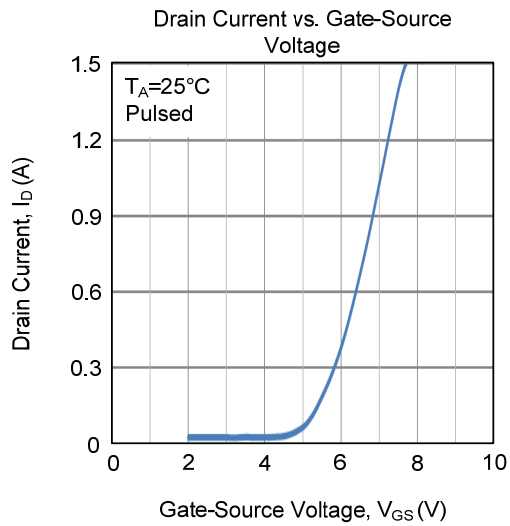
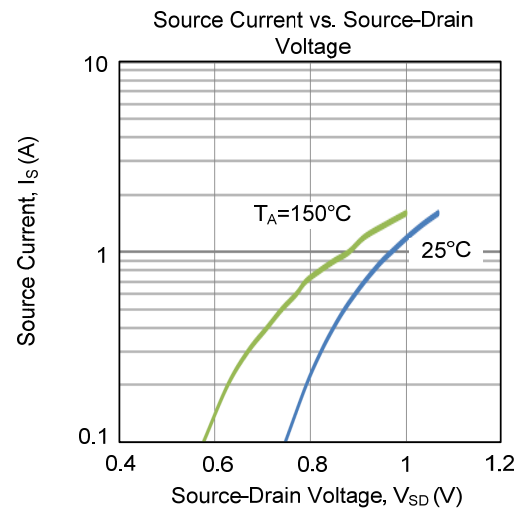
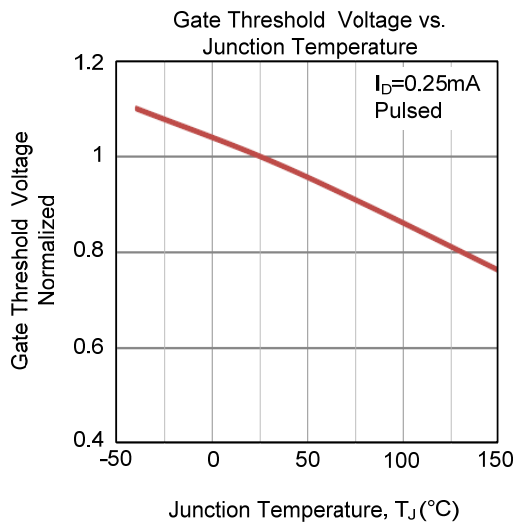


Unclamped Inductive Switching Waveforms

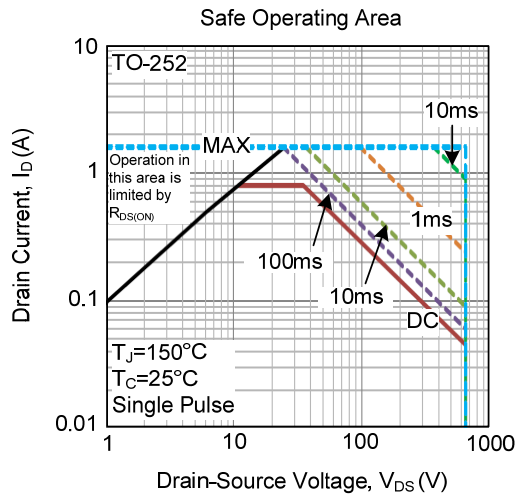
TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.